

SILICON NPN SWITCHING TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH CURRENT CAPABILITY

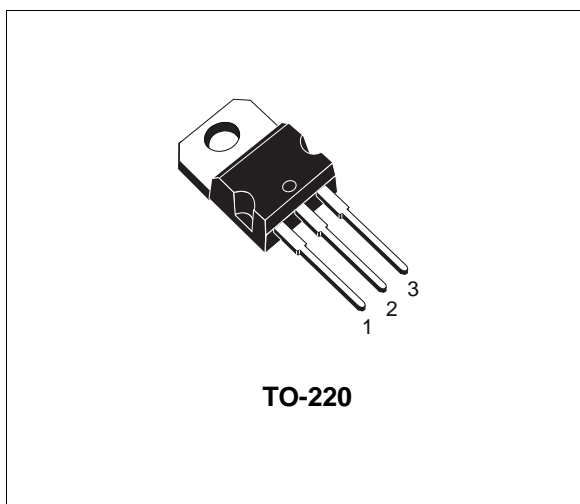
APPLICATIONS

- SWITCHING REGULATORS
- MOTOR CONTROL

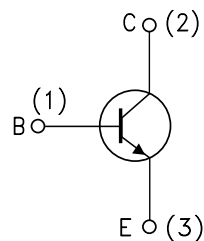
DESCRIPTION

The MJE13007A is silicon multiepitaxial mesa NPN power transistor mounted in Jedec TO-220 plastic package.

They are intended for use in motor control, switching regulators etc.



INTERNAL SCHEMATIC DIAGRAM



SC06960

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage ($V_{BE} = -1.5V$)	850	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	400	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	9	V
I_C	Collector Current	8	A
I_{CM}	Collector Peak Current	16	A
I_B	Base Current	4	A
I_{BM}	Base Peak Current	8	A
I_E	Emitter Current	12	A
I_{EM}	Emitter Peak Current	24	A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$	80	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ C$
T_j	Max. Operating Junction Temperature	150	$^\circ C$

MJE13007A

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.56	°C/W
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ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEV}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = rated V _{CEV} V _{CE} = rated V _{CEV} T _c = 100 °C			1 5	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 9 V			1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage	I _C = 10 mA	400			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 2 A I _B = 0.4 A I _C = 5 A I _B = 1 A I _C = 8 A I _B = 2 A I _C = 5 A I _B = 1 A T _c = 100 °C			1 1.5 3 2	V V V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 2 A I _B = 0.4 A I _C = 5 A I _B = 1 A I _C = 5 A I _B = 1 A T _c = 100 °C			1.2 1.6 1.5	V V V
h _{FE*}	DC Current Gain	I _C = 2 A V _{CE} = 5 V I _C = 5 A V _{CE} = 5 V	8 6		40 30	
f _T	Transition Frequency	I _C = 0.5 A V _{CE} = 10 V f = 1 MHz	4			MHz
C _{CB0}	Output Capacitance	I _E = 0 V _{CB} = 10 V f = 0.1 MHz		110		pF

RESISTIVE LOAD

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _{on}	Turn-on Time	V _{CC} = 125 V I _C = 5 A			0.7	μs
t _s	Storage Time	I _{B1} = -I _{B2} = 1 A t _p = 25 μs Duty Cycle < 1%			3	μs
t _f	Fall Time				0.7	μs

INDUCTIVE LOAD

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _f	Fall Time	V _{CC} = 125 V I _C = 5 A I _{B1} = 1 A t _p = 25 μs Duty Cycle < 1%			0.3	μs
t _f	Fall Time	V _{CC} = 125 V I _C = 5 A I _{B1} = 1 A t _p = 25 μs Duty Cycle < 1% T _c = 100 °C			0.6	μs

* Pulsed: Pulse duration = 300 μs, duty cycle 2 %

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151

